

# ESD Protection diode

## RSA 6.1EN

### ●Application

Noise suppression on signal line

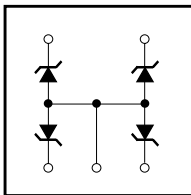
### ●Features

- 1) Small surface mounting type. (UMD5)
- 2) Multiple diodes with common anode configuration.
- 3) High reliability.

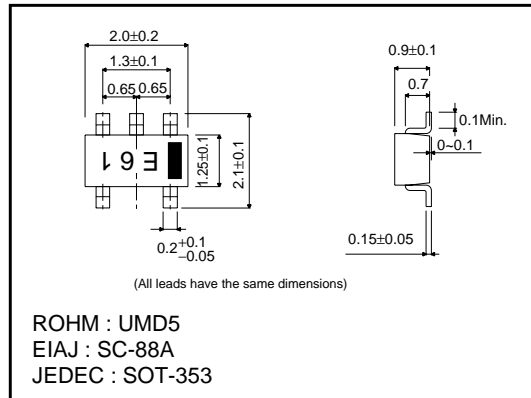
### ●Construction

Silicon epitaxial planar

### ●Circuit



### ●External dimensions (Units : mm)



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak Pulse Power-1 (tp=10×1000μs)	Ppk	30	W
Peak Pulse Power-2 (tp=8×20μs)	Ppk	200	W
Power Dissipation	P	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55~+150	°C

### ●Electrical characteristics (Ta=25°C) \* Rating of per diode.

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Zener voltage	Vz	6.10	—	7.20	V	Iz=1mA
Reverse current	IR	—	—	1	μA	VR=3.0V
Forward current	VF	—	—	1.25	V	IF=200mA
Junction capacitance	Ct	—	90	—	pF	VR=0V, f=1MHz

\* Zener voltage (Vz) shall be measured at 40ms after loading current.

Diodes

●Others

Item	IEC-61000-4-2
Equipment composition	Charge discharge capacitance : 150pF Discharge resistance : 330Ω
Criterion	Repeat by 10 times No erroneous operation Contact : ±9kV In air : ±16kV

●Electrical characteristic curves (Ta=25°C)

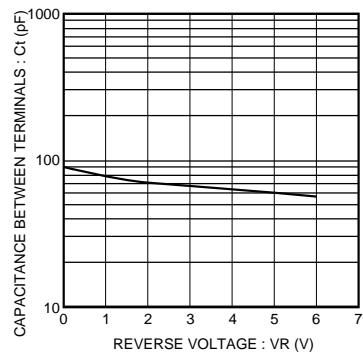


Fig.1 Capacitance Between Terminals Characteristics

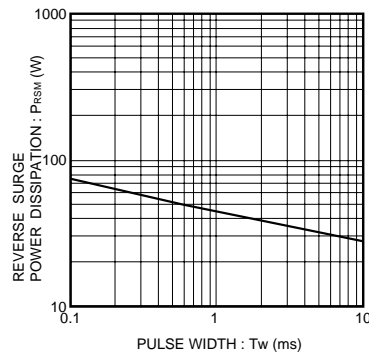


Fig.2 Surge Power Dissipation